

[INTERCONNECTION METHOD AND STRUCTURE]

Abstract of Disclosure

An interconnection structure includes: a dielectric layer; a first metallization pattern on the dielectric layer, the first metallization pattern including at least one etch stop having a perimeter defining at least one etch stop opening; a cured adhesive on a portion of the dielectric layer, the adhesive not present in an area aligned with the at least one etch stop; and at least one electrical device being attached to the dielectric layer by the adhesive such that an active area of the at least one electrical device is aligned with the etch stop perimeter. The active area of the at least one electrical device may further be aligned with at least one predetermined area defined by an optional additional portion of cured adhesive, the additional portion of the cured adhesive being adhesively attached to the dielectric layer and not adhesively attached to the at least one electrical device.